

# **PNP** Darlington Transistor

This device is designed for applications requiring extremely high current gain at currents to 800 mA. Sourced from Process 61.

# Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

| Symbol                            | Parameter  | Value       | Units |
|-----------------------------------|--|-------------|-------|
| V <sub>CES</sub>                  | Collector-Emitter Voltage                        | 30          | V     |
| V <sub>CBO</sub>                  | Collector-Base Voltage                           | 30          | V     |
| V <sub>EBO</sub>                  | Emitter-Base Voltage                             | 10          | V     |
| Ic                                | Collector Current - Continuous                   | 1.2         | A     |
| T <sub>J</sub> , T <sub>stg</sub> | Operating and Storage Junction Temperature Range | -55 to +150 | °C    |

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These resteady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

# Thermal Characteristics TA = 25°C unless otherwise noted

| Symbol                | Characteristic                          |        | Мах      |          |       |
|-----------------------|---|--------|----------|----------|-------|
|                       |   | MPSA64 | *MMBTA64 | **PZTA64 |       |
| P <sub>D</sub>        | Total Device Dissipation                | 625    | 350      | 1,000    | mW    |
|                       | Derate above 25°C                       | 5.0    | 2.8      | 8.0      | mW/°C |
| R <sub>θJC</sub>      | Thermal Resistance, Junction to Case    | 83.3   |          |          | °C/W  |
| $R_{	extsf{	heta}JA}$ | Thermal Resistance, Junction to Ambient | 200    | 357      | 125      | °C/W  |

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

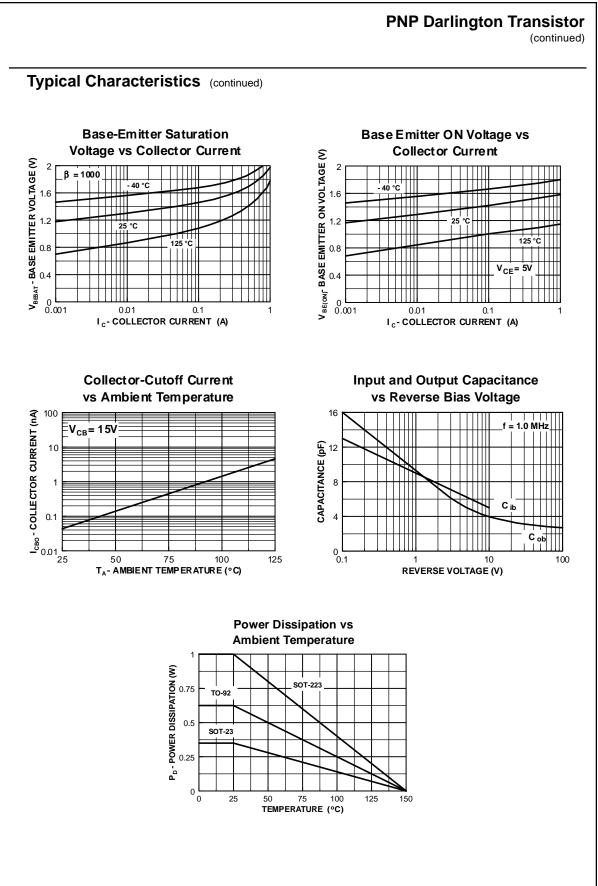
\*\* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

# **PNP** Darlington Transistor

| (continued) | ) |
|-------------|---|
|-------------|---|

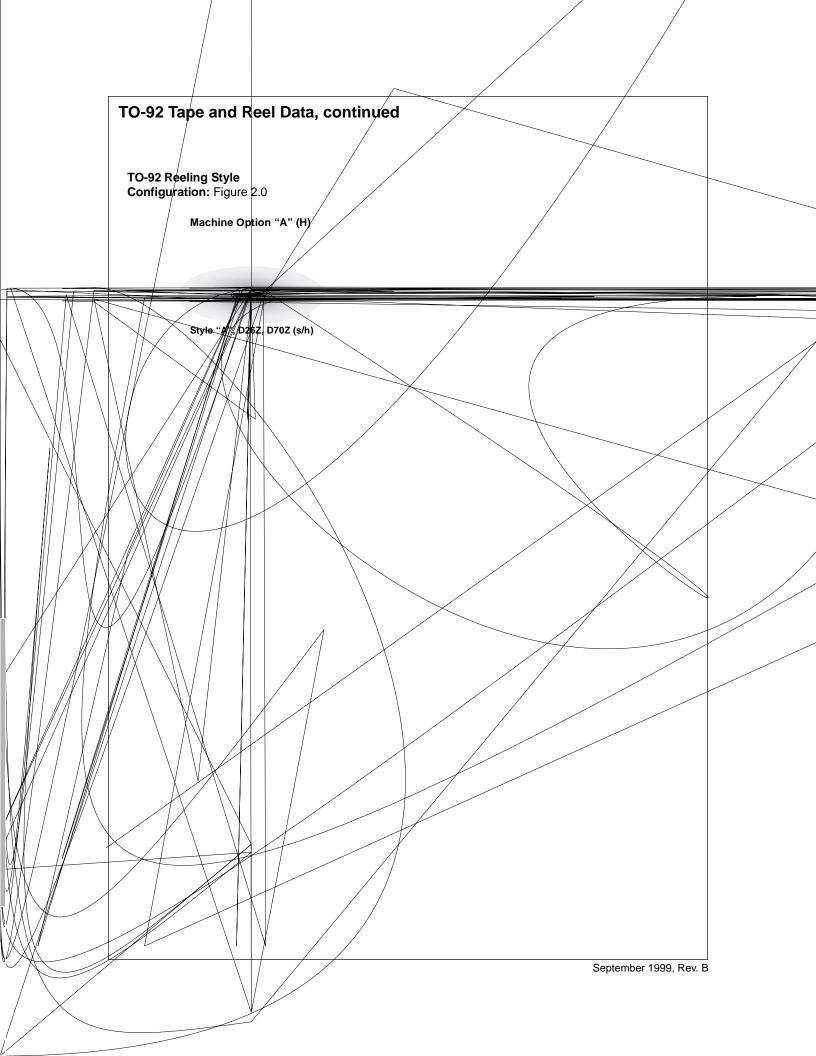
| Symbol                             | Parameter  | Test Conditions   | Min              | Max       | Unit |
|------------------------------------|--|---|------------------|-----------|------|
| FF CHAF                            | RACTERISTICS   |   |                  |           |      |
| (BR)CES                            | Collector-Emitter Breakdown Voltage  | $I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm B} = 0$  | 30               |           | V    |
| BO                                 | Collector-Cutoff Current   | $V_{CB} = 30 \text{ V}, I_E = 0$  |                  | 100       | nA   |
| BO                                 | Emitter-Cutoff Current   | $V_{EB} = 10 \text{ V}, I_{C} = 0$  |                  | 100       | nA   |
| N CHAR                             | ACTERISTICS*   |   |                  |           |      |
| Ē                                  | DC Current Gain  | $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$<br>$I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ | 10,000<br>20,000 |           |      |
| CE(sat)                            | Collector-Emitter Saturation Voltage   | $I_{\rm C}$ = 100 mA, $I_{\rm B}$ = 0.1 mA  |                  | 1.5       | V    |
| BE(on)                             | Base-Emitter On Voltage  | $I_{C}$ = 100 mA, $V_{CE}$ = 5.0 V  |                  | 2.0       | V    |
|                                    |  |   |                  |           |      |
|                                    | GNAL CHARACTERISTICS   | $l_{c} = 10 \text{ mA} \text{ V}_{cr} = 5.0 \text{ V}$  | 125              |           | MHz  |
| *Pulse Test: Pu<br>NOTE: All volta | GNAL CHARACTERISTICS<br>Current Gain - Bandwidth Product<br>Ilse Width ≤ 300 µs, Duty Cycle ≤ 2.0%<br>ges (V) and currents (A) are negative polarity for PNP t | $I_{C}$ = 10 mA, $V_{CE}$ = 5.0 V,<br>f = 100 MHz<br>ransistors.                                    | 125              |           | MH2  |
| *Pulse Test: Pu<br>NOTE: All volta | Current Gain - Bandwidth Product<br>Ilse Width ≤ 300 µs, Duty Cycle ≤ 2.0%<br>ges (V) and currents (A) are negative polarity for PNP t<br>I Characteristics    | f = 100 MHz   |                  | aturation |      |
| *Pulse Test: Pu<br>NOTE: All volta | Current Gain - Bandwidth Product<br>llse Width $\leq$ 300 µs, Duty Cycle $\leq$ 2.0%<br>ges (V) and currents (A) are negative polarity for PNP t               | f = 100 MHz<br>ransistors.<br><b>Collector</b>  | -Emitter Sa      |           |      |

MPSA64 / MMBTA64 / PZTA64



MPSA64 / MMBTA64 / PZTA64







July 1999, Rev. A



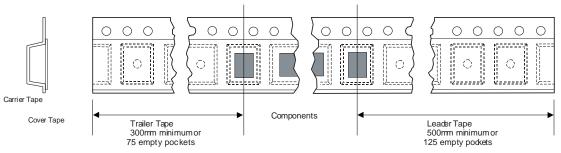
SOT-23 Packaging Configuration: Figure 10

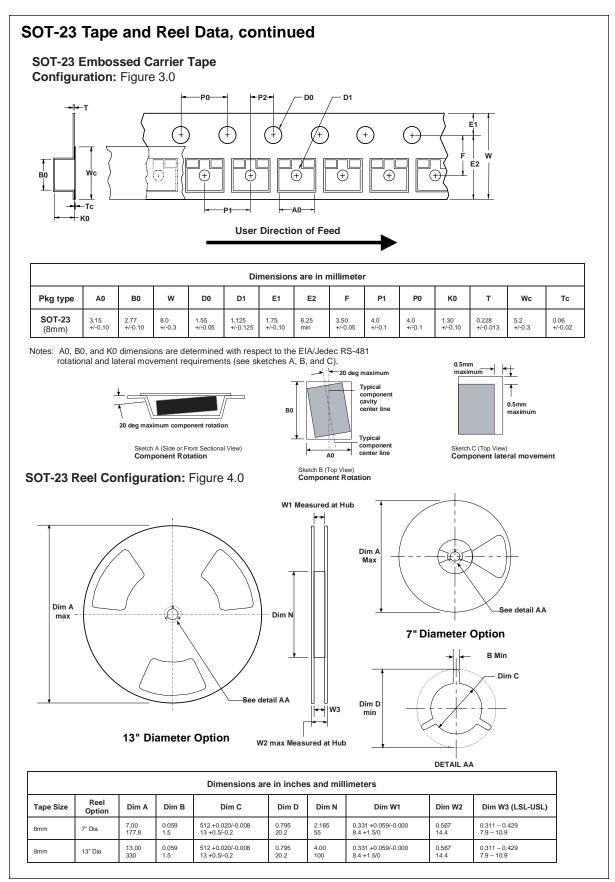
| SOT-23 PackagingInformation |                           |            |  |  |
|-----------------------------|---------------------------|------------|--|--|
| PackagingOption             | Standard<br>(noflow code) | D87Z       |  |  |
| Packagingtype               | TNR                       | TNR        |  |  |
| Qty per Reel/Tube/Bag       | 3,000                     | 10,000     |  |  |
| Reel Size                   | 7" Dia                    | 13"        |  |  |
| Box Dimension (mm)          | 187x107x183               | 343x343x64 |  |  |
| Max qty per Box             | 24,000                    | 30,000     |  |  |
| Weight per unit (gm)        | 0.0082                    | 0.0082     |  |  |
| Weight per Reel (kg)        | 0.1175                    | 0.4006     |  |  |
| Note/Comments               |                           |            |  |  |



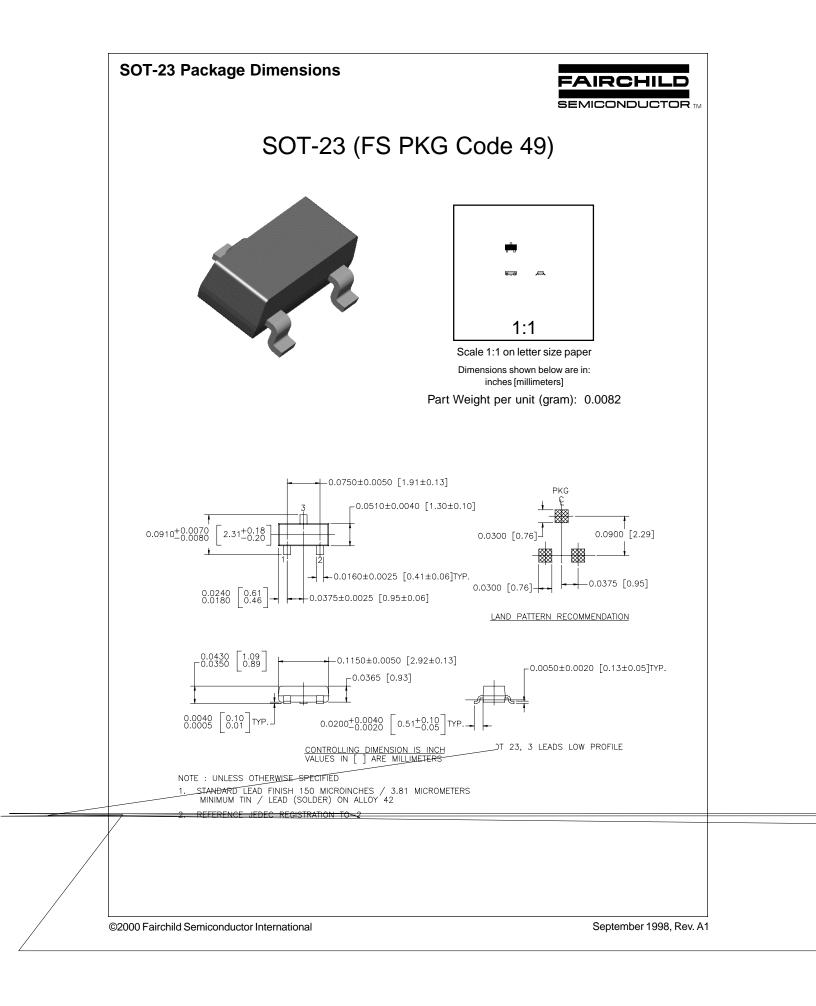


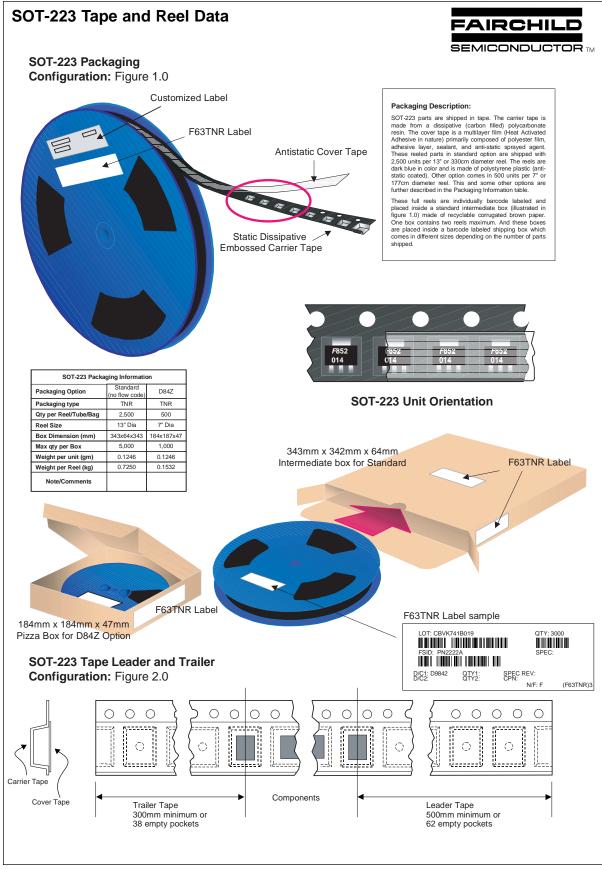
# SOT-23 Tape Leader and Trailer Configuration: Figure 20





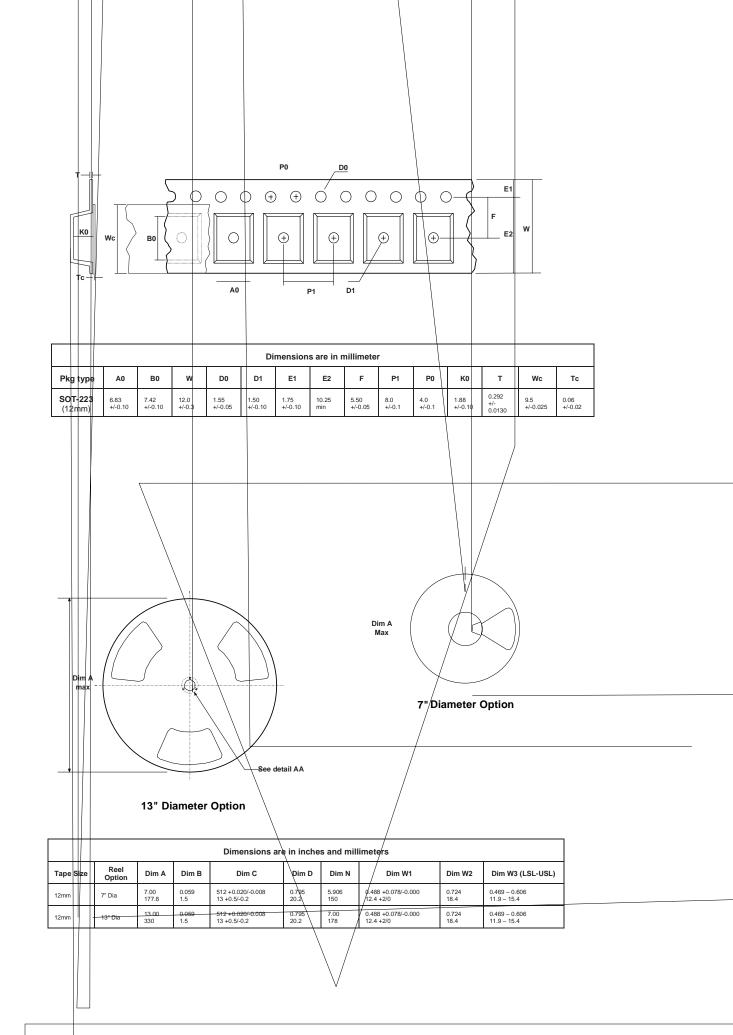
September 1999, Rev. C



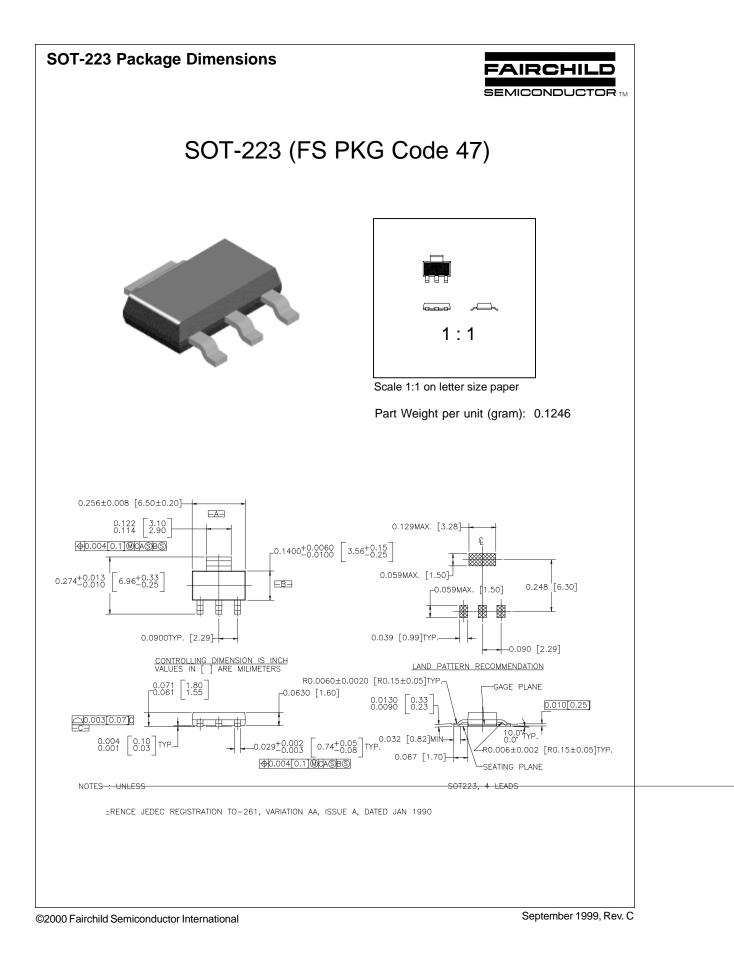


©2000 Fairchild Semiconductor International

September 1999, Rev. B



Dim N



### TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™ Bottomless™ CoolFET™ CROSSVOLT™ DOME™ E<sup>2</sup>CMOS<sup>™</sup> EnSigna™ FACT™ FACT Quiet Series<sup>™</sup> FAST<sup>®</sup>

FASTr™ GlobalOptoisolator™ GTO™ HiSeC™ **ISOPLANAR™** MICROWIRE™ OPTOLOGIC™ **OPTOPLANAR™** PACMAN™ POP™

PowerTrench<sup>®</sup> QFET™ QS™ QT Optoelectronics<sup>™</sup> Quiet Series<sup>™</sup> SILENT SWITCHER® SMART START™ SuperSOT<sup>™</sup>-3 SuperSOT<sup>™</sup>-6 SuperSOT<sup>™</sup>-8

SyncFET™ TinyLogic™ UHC™ VCX™

## DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

#### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

### PRODUCT STATUS DEFINITIONS

**Definition of Terms** 

| Datasheet Identification | Product Status            | Definition  |
|--------------------------|---------------------------|---|
| Advance Information      | Formative or<br>In Design | This datasheet contains the design specifications for<br>product development. Specifications may change in<br>any manner without notice.  |
| Preliminary              | First Production          | This datasheet contains preliminary data, and<br>supplementary data will be published at a later date.<br>Fairchild Semiconductor reserves the right to make<br>changes at any time without notice in order to improve<br>design. |
| No Identification Needed | Full Production           | This datasheet contains final specifications. Fairchild<br>Semiconductor reserves the right to make changes at<br>any time without notice in order to improve design.   |
| Obsolete                 | Not In Production         | This datasheet contains specifications on a product<br>that has been discontinued by Fairchild semiconductor.<br>The datasheet is printed for reference information only.   |
|                          | 1                         | Rev G   |